What is claimed is:

1. A pixel structure of an active matrix organic light emitting diode (OLED) display, comprising:

a first transistor having a gate terminal coupled to a scan signal and a drain terminal coupled to a data signal, the first transistor switching the transmission of the data signal according to the scan signal;

a storage capacitor having two terminals coupled to a source terminal of the first transistor and a reference node, the reference node having a second voltage;

a second transistor having a gate terminal coupled to the source terminal of the first transistor and a source terminal coupled to the reference node; and

an OLED having a cathode coupled to a drain terminal of the second transistor and an anode coupled to a first voltage exceeding the second voltage;

wherein the first transistor or the second transistor is an amorphous silicon thin film transistor (a-Si TFT), and a light efficiency of the OLED is no less than 11cd/A.

2. The pixel structure as claimed in claim 1, wherein the OLED is made of C545T.

3. The pixel structure as claimed in claim 1, wherein the OLED is made of Irppy.

4. The pixel structure as claimed in claim 1, wherein the second voltage is a ground.

5. An active matrix organic light emitting diode (OLED) display, comprising:

a panel, comprising a plurality of pixels, each pixel comprising a first transistor having a gate terminal coupled to a scan signal and a drain terminal coupled to a data signal, the first transistor switching the transmission of the data signal according to the scan signal; a storage capacitor having two terminals coupled to a source terminal of the first transistor and a reference node, the reference node having a second voltage; a second transistor having a gate terminal coupled to the source terminal of the first transistor and a source terminal coupled to the reference node; and an OLED having a cathode coupled to a drain terminal of the second transistor and an anode coupled to a first voltage, the first voltage exceeding the second voltage; wherein the first transistor or the second transistor is an amorphous silicon thin film transistor (a-Si TFT), and a light efficiency of the OLED is no less than 11cd/A.

6. The pixel structure as claimed in claim 5, wherein the OLED is made of C545T.

7. The pixel structure as claimed in claim 5, wherein the OLED is made of Irppy.

8. The pixel structure as claimed in claim 5, wherein the second voltage is a ground.

9. A pixel structure of an active matrix organic light emitting diode (OLED) display, comprising:

a first transistor having a gate terminal coupled to a scan signal and a drain terminal coupled to a data signal, the first transistor switching the transmission of the data signal according to the scan signal;

a storage capacitor having two terminals coupled to a source terminal of the first transistor and a reference node, the reference node having a second voltage;

a second transistor having a gate terminal coupled to the source terminal of the first transistor and a drain terminal coupled to the reference node; and

an OLED having an anode coupled to a source terminal of the second transistor and a cathode coupled to a first voltage less than the second voltage;

wherein the first transistor or the second transistor is an amorphous silicon thin film transistor (a-Si TFT), and a light efficiency of the OLED is no less than 11cd/A.

10. The pixel structure as claimed in claim 9, wherein the OLED is made of C545T.

11. The pixel structure as claimed in claim 9, wherein the OLED is made of Irppy.

12. The pixel structure as claimed in claim 9, wherein the second voltage is a high voltage.

13. An active matrix organic light emitting diode (OLED) display, comprising:

a panel, comprising a plurality of pixels, each pixel comprising a first transistor having a gate terminal coupled to a scan signal and a drain terminal coupled to a data signal, the first transistor switching the transmission of the data signal according to the scan signal; a storage capacitor having two terminals coupled to a source terminal of the first transistor and a reference node, the reference node having a second voltage; a second transistor having a gate terminal coupled to the source terminal of the first transistor and a drain terminal coupled to the reference node; and an OLED having an anode coupled to a source terminal of the second transistor and a cathode coupled to a first voltage less than the second voltage; wherein the first transistor or the second transistor is an amorphous silicon thin film transistor (a-Si TFT), and a light efficiency of the OLED is no less than 11cd/A.

14. The pixel structure as claimed in claim 13, wherein the OLED is made of C545T.

15. The pixel structure as claimed in claim 13, wherein the OLED is made of Irppy.

16. The pixel structure as claimed in claim 13, wherein the second voltage is a high voltage.